

# MA2C858

## Silicon epitaxial planar type

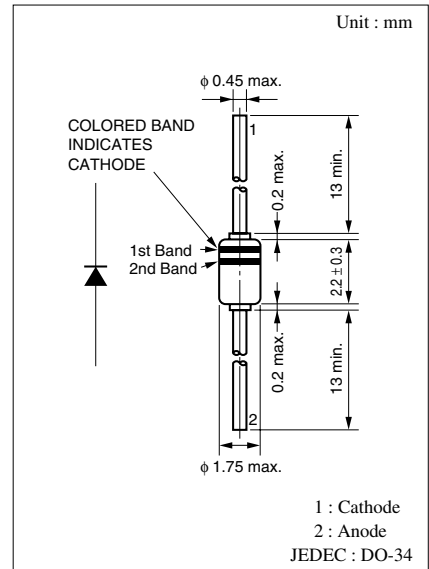
For band switching

### ■ Features

- Extra-small DHD envelope, allowing to insert into a 5 mm pitch hole.
- Less voltage dependence of the terminal capacitance  $C_t$
- Low forward dynamic resistance  $r_f$
- Optimum for a band switching of a tuner

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	35	V
Forward current (DC)	$I_F$	100	mA
Operating ambient temperature	$T_{opr}$	-25 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +100	$^\circ\text{C}$



### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)*	$I_R$	$V_R = 33 \text{ V}$			100	nA
Forward voltage (DC)	$V_F$	$I_F = 100 \text{ mA}$			1	V
Terminal capacitance	$C_t$	$V_R = 6 \text{ V}, f = 1 \text{ MHz}$			1.2	pF
Forward dynamic resistance	$r_f$	$I_F = 2 \text{ mA}, f = 100 \text{ MHz}$			0.9	$\Omega$

Note) 1. Rated input/output frequency: 100 MHz  
2. \*: Measurement in light shielded condition

### ■ Cathode Indication

Type No.		MA2C858
Color	1st Band	Yellow
	2nd Band	Yellow

